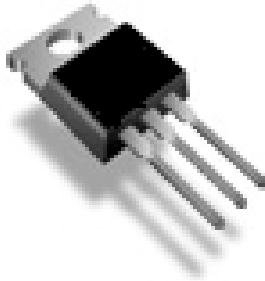




Description

The Bay Linear MOSFET's provide the designers with the best combination of fast switching, ruggedized device design, low On-resistance and low cost-effectiveness.

The TO-220 is offered in a 3-pin is universally preferred for all commercial-industrial applications at power dissipation level to approximately to 50 Watts. Also, available in a D² surface mount power package with a power dissipation up to 2 Watts.



Features

- **Dynamic dv/dt Rating**
- **Repetitive Avalanche Rated**
- **Fast Switching**
- **Ease of Paralleling**
- **Simple Drive Requirements**

$$V_{DSS} = 100V$$

$$R_{DS(ON)} = 0.077 \Omega$$

$$I_D = 28A$$

Ordering Information

Device	Package	Temp.
IRL540T	TO-220	0 to 150°C
IRL540S	TO-263 (D ²)	0 to 150°C

Absolute Maximum Rating

	Parameter	Max	Unit
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	28	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	20	
I_{DM}	Pulsed Drain Current	110	
$P_D @ T_C = 25^\circ C$	Power Dissipation	150	W
$P_D @ T_A = 25^\circ C$	Power Dissipation (PCB Mount, D ²) (1)	3.7	
	Linear Derating Factor	1.0	W/°C
	Linear Derating Factor (PCB Mount, D ²) (1)	0.025	
V_{GS}	Gate-to- Source Voltage (TO-220)	±20	V
V_{GS}	Gate-to- Source Voltage (D ²)	±10	
E_{AS}	Single Pulse Avalanche Energy (TO-220) (2a)	230	mJ
E_{AS}	Single Pulse Avalanche Energy (D2) (2b)	440	
I_{AR}	Avalanche Current	28	A
E_{AR}	Repetitive Avalanche Energy	15	mJ
dv/dt	Peak Diode Recovery dv/dt	5.5	V/ns
T_J, T_{STG}	Junction & Storage Temperature Range	-55 to +175	°C
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	

Thermal Resistance

	Parameter	Min	Typ	Max	Units
$R_{\theta JC}$	Junction-to Case	-	-	1.0	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface (TO-220)	-	0.50	-	
$R_{\theta JA}$	Junction-to Ambient (PCB Mount, D ²)	-	-	40	
$R_{\theta JA}$	Junction-to Ambient	-	-	62	

Electrical Characteristics ($T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
$V_{(BR)DSS}$	Drain-to-source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	100			V
$V_{(BR)DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	Reference to 25°C , $I_D = 1mA$	-	0.13	-	V/ $^\circ\text{C}$
$I_{D(ON)}$	On-State Drain Current (note 2)	$V_{GS} > I_{D(ON)} \times R_{DS(ON)Max}$			28	A
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance	TO-220: $V_{GS} = 10V, I_D = 17A$ D^2 : $V_{GS} = 5V, I_D = 17A$ (note 4)			0.077	Ω
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.0	-	-	V
g_{fs}	Forward Transconductance	$V_{DS} = 50V, I_D = 17A$	8.7	-	-	S
I_{DSS}	Drain-to-Source Leakage Current	$V_{DS}=100V, V_{GS}=0V$	-	-	25	μA
		$V_{DS}=80V, V_{GS}=0V, T_J=150^\circ\text{C}$	-	-	250	
I_{GSS}	Gate-to-Source Forward Leakage	$V_{GS} = 20V$	-	-	100	nA
	Gate-to-Source Reverse Leakage	$V_{GS} = -20V$	-	-	-100	
Q_G	Total Gate Charge	$I_D=17V$	-	-	72	nC
Q_{gs}	Gate-to-Source Charge	$V_{DS}=80V$	-	-	11	
$t_{d(on)}$	Turn-On Delay Time	$V_{DD}=50V$	-	11	-	ns
t_f	Fall Time	$R_D=2.9$	-	43	-	
$t_{d(off)}$	Turn-Off Delay Time	$R_G=9.1\Omega$	-	53	-	
t_r	Rise Time	$I_D=17A$	-	44	-	
L_D	Internal Drain Inductance	Between lead 6mm(0.25in.) from package and center or die contact	-	4.5	-	nH
L_S	Internal Source Inductance		-	7.5	-	
C_{iss}	Input Capacitance	$V_{GS}=0V$	-	1700	-	pF
C_{oss}	Output Capacitance	$V_{DS}=25V$	-	560	-	
C_{rss}	Reverse Transfer Capacitance	$F=1.0MHz$	-	120	-	

Source-Drain Rating Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Units
I_S	Continuous Source Current (Body Diode)	MOSFET symbol showing the integral reverse p-n junction diode.	-	-	28	A
I_{SM}	Pulsed Source Current (Body Diode)		-	-	110	
V_{SD}	Diode Forward Voltage	$T_J=25^\circ\text{C}, I_S=28A, V_{GS}=DV$	-	-	2.5	V
t_{rr}	Reverse Recovery Time	$T_J=25^\circ\text{C}, I_F=17A$	-	180	360	ns
Q_{rr}	Reverse Recovery Charge	$di/dt=100A/\mu s$	-	1.3	2.8	μC
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by (L_S+L_D))				

Notes: 1. Repetitive Rating; pulse width limited by max. junction temperature.

2a. $V_{DD} = 25V$, starting $T_J = 25^\circ\text{C}$, $L = 440\mu H$, $R_G = 25\Omega$, $I_{AS} = 28A$

2b. $V_{DD} = 25V$, starting $T_J = 25^\circ\text{C}$, $L = 841\mu H$, $R_G = 25\Omega$, $I_{AS} = 28A$

3. $I_{SD} \leq 28A$, $di/dt \leq 170A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 150^\circ\text{C}$

4. Pulse with $\leq 300\mu s$; duty cycle $\leq 2\%$

Advance Information- These data sheets contain descriptions of products that are in development. The specifications are based on the engineering calculations, computer simulations and/ or initial prototype evaluation.

Preliminary Information- These data sheets contain minimum and maximum specifications that are based on the initial device characterizations. These limits are subject to change upon the completion of the full characterization over the specified temperature and supply voltage ranges.

The application circuit examples are only to explain the representative applications of the devices and are not intended to guarantee any circuit design or permit any industrial property right to other rights to execute. Bay Linear takes no responsibility for any problems related to any industrial property right resulting from the use of the contents shown in the data book. Typical parameters can and do vary in different applications. Customer's technical experts must validate all operating parameters including "Typical" for each customer application.

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